TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892 (REV. 3-78) — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

NOTICE OF REFERENCES CITED

SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER
697830	258	2

APPLICANT(S): Huang et al

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	A	4,916,498	4/10/90	Berenz	357	22A	
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	M	63-318165	12/88	Japan	Yamane	357	22A		
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Loke	10/16/91

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)